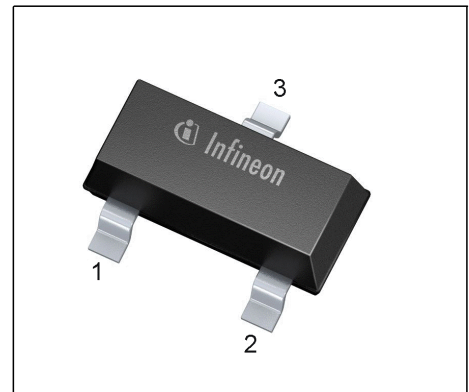


## Low Noise Silicon Bipolar RF Transistor

- High linearity low noise RF transistor
- 22 dBm OP1dB and 31 dBm OIP3  
@ 900 MHz, 8 V, 70 mA
- For UHF / VHF applications
- Driver for multistage amplifiers
- For linear broadband and antenna amplifiers
- Collector design supports 5 V supply voltage
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available



**ESD (Electrostatic discharge) sensitive device, observe handling precaution!**

Type	Marking	Pin Configuration			Package
BFR106	R7s	1=B	2=E	3=C	SOT23

**Maximum Ratings** at  $T_A = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_A = 25\text{ °C}$ $T_A = -55\text{ °C}$	$V_{CEO}$	16 15	V
Collector-emitter voltage	$V_{CES}$	20	
Collector-base voltage	$V_{CBO}$	20	
Emitter-base voltage	$V_{EBO}$	3	
Collector current	$I_C$	210	mA
Base current	$I_B$	21	
Total power dissipation <sup>1)</sup> $T_S \leq 76\text{ °C}$	$P_{tot}$	700	mW
Junction temperature	$T_J$	150	°C
Storage temperature	$T_{Stg}$	-55 ... 150	

### Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>2)</sup>	$R_{thJS}$	105	K/W

<sup>1)</sup>  $T_S$  is measured on the collector lead at the soldering point to the pcb

<sup>2)</sup> For calculation of  $R_{thJS}$  please refer to Application Note AN077 (Thermal Resistance Calculation)

**Electrical Characteristics** at  $T_A = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}$ , $I_B = 0$	$V_{(BR)CEO}$	15	-	-	V
Collector-emitter cutoff current $V_{CE} = 20\text{ V}$ , $V_{BE} = 0$ $V_{CE} = 10\text{ V}$ , $V_{BE} = 0$	$I_{CES}$	- -	- 0.001	1 0.03	$\mu\text{A}$
Collector-base cutoff current $V_{CB} = 10\text{ V}$ , $I_E = 0$	$I_{CBO}$	-	1	30	nA
Emitter-base cutoff current $V_{EB} = 2\text{ V}$ , $I_C = 0$	$I_{EBO}$	-	1	30	
DC current gain $I_C = 70\text{ mA}$ , $V_{CE} = 8\text{ V}$ , pulse measured	$h_{FE}$	70	100	140	-

**Electrical Characteristics** at  $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 70\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $f = 500\text{ MHz}$	$f_T$	3.5	5	-	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$ , $V_{BE} = 0$ , emitter grounded	$C_{cb}$	-	0.85	1.2	pF
Collector emitter capacitance $V_{CE} = 10\text{ V}$ , $f = 1\text{ MHz}$ , $V_{BE} = 0$ , base grounded	$C_{ce}$	-	0.27	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$ , $f = 1\text{ MHz}$ , $V_{CB} = 0$ , collector grounded	$C_{eb}$	-	3.9	-	
Minimum noise figure $I_C = 20\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ , $f = 900\text{ MHz}$ $I_C = 20\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ , $f = 1.8\text{ GHz}$	$NF_{min}$	-  -	1.8  3	-  -	dB

**Electrical Characteristics** at  $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

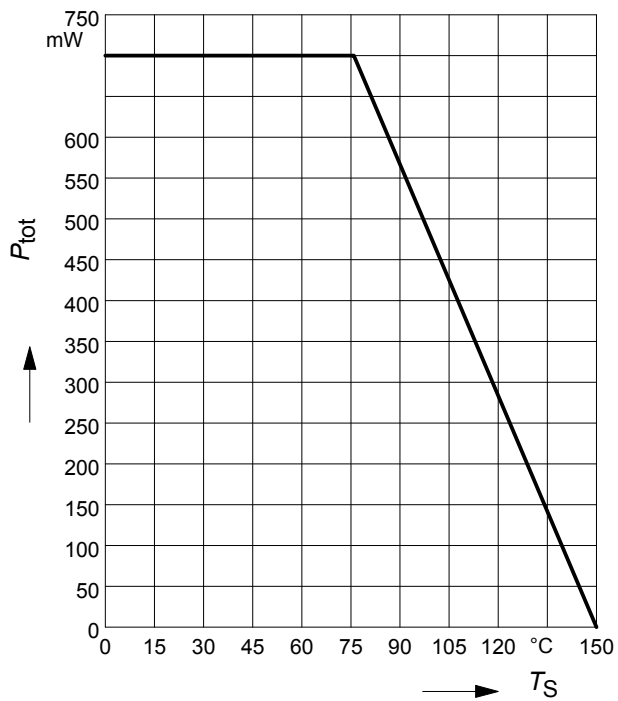
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Power gain, maximum available <sup>1)</sup> $I_C = 70\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$ , $f = 900\text{ MHz}$ $I_C = 70\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$ , $f = 1.8\text{ GHz}$	$G_{ma}$	-	13	-	dB
Transducer gain $I_C = 70\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_L = 50\text{ }\Omega$ , $f = 900\text{ MHz}$ $I_C = 70\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S = Z_L = 50\text{ }\Omega$ , $f = 1.8\text{ GHz}$	$ S_{21e} ^2$	-	10.5	-	dB
Third order intercept point at output <sup>2)</sup> $V_{CE} = 8\text{ V}$ , $I_C = 70\text{ mA}$ , $f = 0.9\text{ GHz}$ , $Z_S=Z_L=50\Omega$	$IP_3$	-	31	-	dBm
1dB compression point $I_C = 70\text{ mA}$ , $V_{CE} = 8\text{ V}$ , $Z_S=Z_L=50\Omega$ , $f = 0.9\text{ GHz}$	$P_{-1dB}$	-	22	-	

$$^1G_{ma} = |S_{21e}| / |S_{12e}| (k - (k^2 - 1)^{1/2})$$

<sup>2)</sup> $IP_3$  value depends on termination of all intermodulation frequency components.

Termination used for this measurement is  $50\text{ }\Omega$  from  $0.1\text{ MHz}$  to  $6\text{ GHz}$

Total power dissipation  $P_{\text{tot}} = f(T_S)$

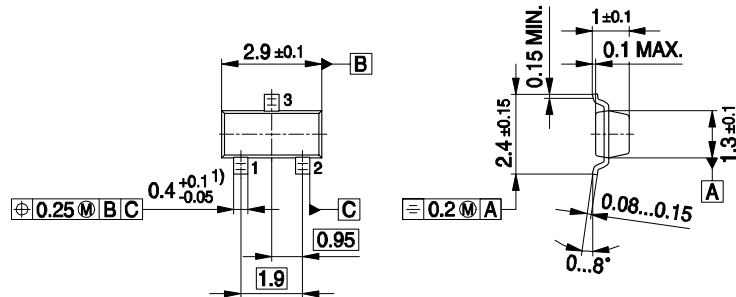
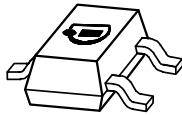


**SPICE GP Model**

For the SPICE Gummel Poon (GP) model as well as for the S-parameters (including noise parameters) please refer to our internet website [www.infineon.com/rf.models](http://www.infineon.com/rf.models).

Please consult our website and download the latest versions before actually starting your design.

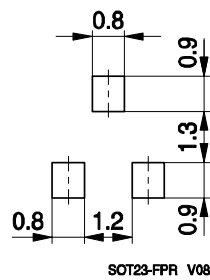
## Package Outline



1) Lead width can be 0.6 max. in dambar area

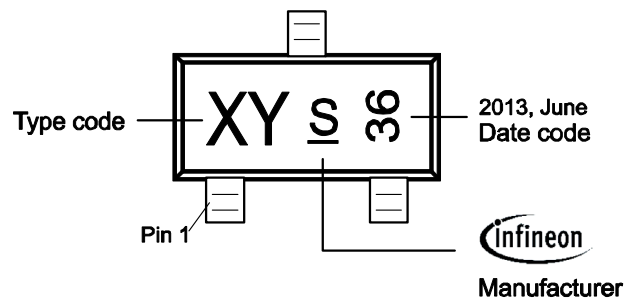
SOT23-PO V08

## Foot Print



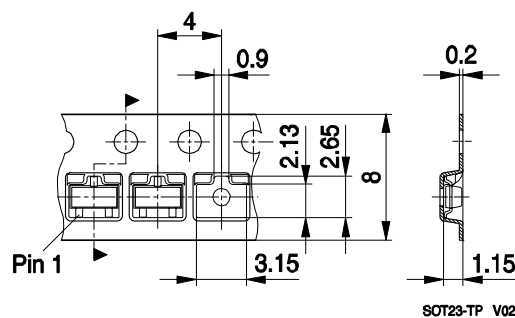
SOT23-FPR V08

## Marking Layout



## Standard Packing

Reel o 180 mm: 3.000 Pieces / Reel  
Reel o 330 mm = 10.000 Pieces / Reel



SOT23-TP V02

**Edition 2009-11-16**

**Published by  
Infineon Technologies AG  
81726 Munich, Germany**

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